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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO

OTHER DOCUMENTS

SL	Article entitled: Nb Oxide Thin Film Resistors; by Wilson <i>et al.</i> , published in IEEE Transactions on Applied Superconductivity, Vol.9 No. 2, June 1999.
SL	Article entitled: Properties of Ru-Ta Alloys as Gate Electrodes For NMOS and PMOS Silicon Devices, by Zhong <i>et al.</i> , IEEE, 2001
SL	Article entitled: Tunable Work Function Molybdenum Gate Technology for FDSOI-CMOS, by Ranade <i>et al.</i> , IEEE 2002
SL	Article entitled: A Phase Map for Sputter Deposited Niobium Oxides, by Lee and Aita, published in the Journal of Applied Physics, Vol. 70, No. 4, 15 August 1991

EXAMINER

/Steven Loke/

DATE CONSIDERED

05/10/2006